



100V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _{D MAX} T _C = +25°C
100\/	8.5mΩ @ V _{GS} = 10V	55A
100V	12.5mΩ @ V _{GS} = 4.5V	45A

Description

This MOSFET is designed to minimize the on-state resistance $(R_{DS(ON)})$ yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

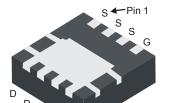
- Synchronous Rectifier
- Backlighting
- · Power Management Functions
- DC-DC Converters

Features and Benefits

- Low R_{DS(ON)} Ensures On State Losses are Minimized
- Excellent Q_{gd} × R_{DS(ON)} Product (FOM)
- Advanced Technology for DC/DC Converters
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies Just 33% of the Board Area Occupied by SO-8 Enabling Smaller End Product
- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen- and Antimony-Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

Mechanical Data

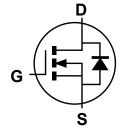
- Case: PowerDI[®]3333-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Lead-Frame. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.034 grams (Approximate)







Top View



Equivalent Circuit

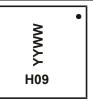
Ordering Information (Note 4)

Part Number	Case	Packaging
DMTH10H009LFG-7	PowerDI3333-8	2,000/Tape & Reel
DMTH10H009LFG-13	PowerDI3333-8	3,000/Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



PowerDI3333-8

H09 = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 20 = 2020) WW = Week Code (01 to 53)



Maximum Ratings (@ T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V _{DSS}	100	V
Gate-Source Voltage		V _{GSS}	±20	V
Operation of the Comment (Nets 5) V 40V	T _A = +25°C T _A = +100°C	I _D	14 10	А
Continuous Drain Current (Note 5) V _{GS} = 10V	T_{C} = +25°C T_{C} = +100°C	l _D	55 39	А
Maximum Continuous Body Diode Forward Current (Note 5	Is	30	Α	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	220	Α	
Pulsed Body Diode Continuous Current (10µs Pulse, Duty 0	I _{SM}	220	Α	
Avalanche Current (L = 1mH)		I _{AS}	17	Α
Avalanche Energy (L = 1mH)		E _{AS}	144.5	mJ

Thermal Characteristics (@ T_A = +25°C, unless otherwise specified.)

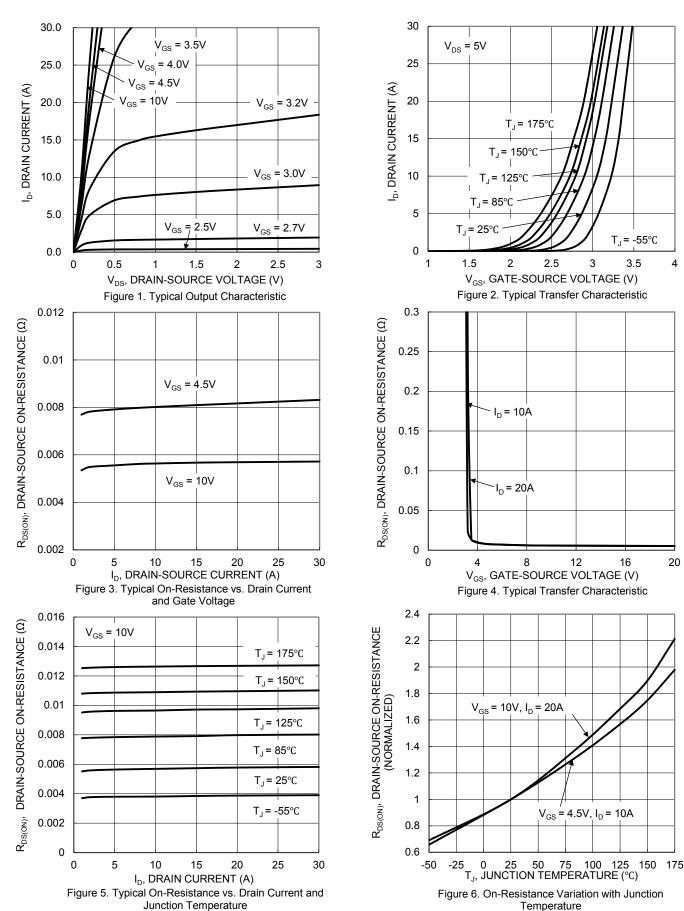
Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5) $T_A = +25^{\circ}C$		P_{D}	2.5	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{ hetaJA}$	60	°C/W	
Total Power Dissipation	P_{D}	39	W	
Thermal Resistance, Junction to Case		$R_{ heta JC}$	3.8	°C/W
Operating and Storage Temperature Range		$T_{J_i} T_{STG}$	-55 to +175	°C

Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 6)							
Drain-Source Breakdown Voltage	BV _{DSS}	100	-	_	V	$V_{GS} = 0V$, $I_D = 1mA$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μA	$V_{DS} = 80V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 6)				•	•		
Gate Threshold Voltage	$V_{GS(TH)}$	1.1	_	2.5	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain Source On Registence		_	6.4	8.5	mΩ	V _{GS} = 10V, I _D = 20A	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	8.2	12.5	11177	V _{GS} = 4.5V, I _D = 10A	
Diode Forward Voltage	V_{SD}	_	0.8	1.2	V	$V_{GS} = 0V, I_S = 20A$	
DYNAMIC CHARACTERISTICS (Note 7)							
Input Capacitance	C _{iss}	1	2361	_		V _{DS} = 50V, V _{GS} = 0V f = 1MHz	
Output Capacitance	Coss	-	611	_	pF		
Reverse Transfer Capacitance	Crss	_	16	_			
Gate Resistance	R_g	_	1.7	_	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz	
Total Gate Charge	Qg	_	41	_		V - 50V I - 42A	
Gate-Source Charge	Qgs	_	7.3	_	nC	$V_{DD} = 50V, I_D = 13A,$ $V_{GS} = 10V$	
Gate-Drain Charge	Q_{gd}	_	9.3	_		VGS - 10V	
Turn-On Delay Time	t _{D(ON)}	_	7	_		V _{DD} = 50V, V _{GS} = 10V,	
Turn-On Rise Time	t _R	_	12	_	no		
Turn-Off Delay Time	t _{D(OFF)}	_	42	_	ns	$I_D = 13A, R_g = 6\Omega$	
Turn-Off Fall Time	t _F	_	24	_			
Reverse Recovery Time	t _{RR}	_	45	_	ns	100 4:/44 - 1000/	
Reverse Recovery Charge	Q _{RR}	_	68	_	nC	I _F = 13A, di/dt = 100A/μs	

 Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing. Notes:







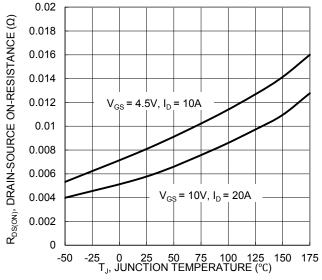
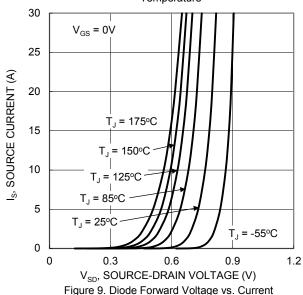


Figure 7. On-Resistance Variation with Junction Temperature



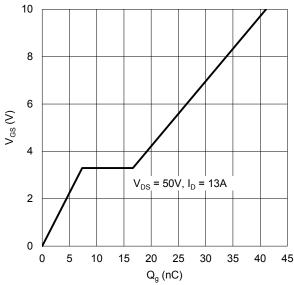


Figure 11. Gate Charge

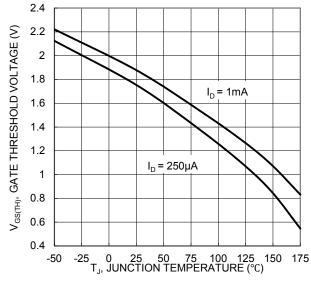
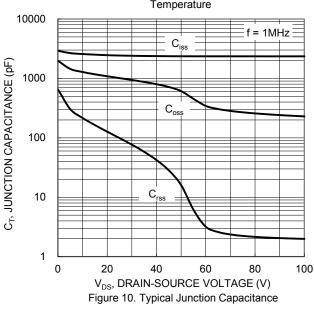
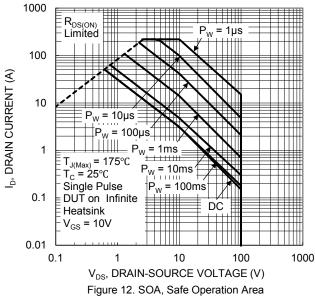


Figure 8. Gate Threshold Variation vs. Junction Temperature







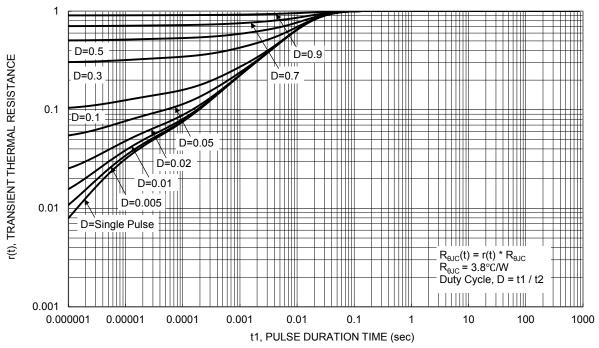


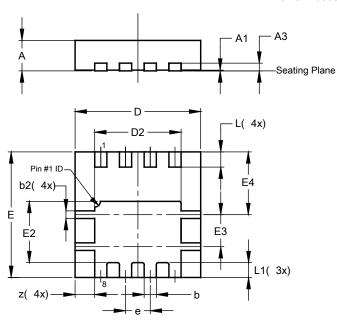
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8

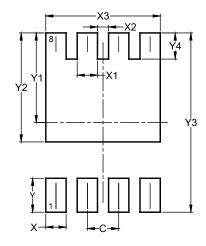


PowerDI3333-8					
Dim	Min	Max	Тур		
Α	0.75	0.85	0.80		
A1	0.00	0.05	0.02		
A3	-	-	0.203		
b	0.27	0.37	0.32		
b2	0.15	0.25	0.20		
D	3.25	3.35	3.30		
D2	2.22	2.32	2.27		
Е	3.25	3.35	3.30		
E2	1.56	1.66	1.61		
E3	0.79	0.89	0.84		
E4	1.60	1.70	1.65		
е	_	_	0.65		
L	0.35	0.45	0.40		
L1	_	_	0.39		
Z	_	_	0.515		
All Dimensions in mm					

Suggested Pad Layout

 $Please see \ http://www.diodes.com/package-outlines.html \ for \ the \ latest \ version.$

PowerDI3333-8



Dimensions	Value (in mm)
С	0.650
Х	0.420
X1	0.420
X2	0.230
Х3	2.370
Υ	0.700
Y1	1.850
Y2	2.250
Y3	3.700
Y4	0.540



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